

General Purpose Transistor

BCW70LT1G

PNP Silicon

Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

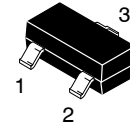
Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-45	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-100	mAdc

THERMAL CHARACTERISTICS

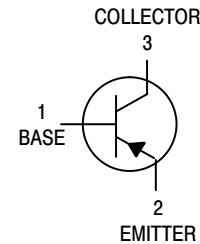
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

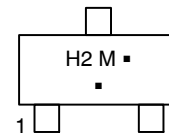
- FR-5 = 1.0 x 0.75 x 0.062 in.
- Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



H2 = Device Code
M = Date Code*
■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
BCW70LT1G	SOT-23 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage ($I_C = -2.0\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	-45	–	Vdc
Collector-Emitter Breakdown Voltage ($I_C = -100\text{ }\mu\text{Adc}$, $V_{EB} = 0$)	$V_{(BR)CES}$	-50	–	Vdc
Emitter-Base Breakdown Voltage ($I_E = -10\text{ }\mu\text{Adc}$, $I_C = 0$)	$V_{(BR)EBO}$	-5.0	–	Vdc
Collector Cutoff Current ($V_{CB} = -20\text{ Vdc}$, $I_E = 0$) ($V_{CB} = -20\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$)	I_{CBO}	– –	-100 -10	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = -2.0\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$)	h_{FE}	215	500	–
Collector-Emitter Saturation Voltage ($I_C = -10\text{ mAdc}$, $I_B = -0.5\text{ mAdc}$)	$V_{CE(sat)}$	–	-0.3	Vdc
Base-Emitter On Voltage ($I_C = -2.0\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$)	$V_{BE(on)}$	-0.6	-0.75	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Output Capacitance ($I_E = 0$, $V_{CB} = -10\text{ Vdc}$, $f = 1.0\text{ MHz}$)	C_{obo}	–	7.0	pF
Noise Figure ($I_C = -0.2\text{ mAdc}$, $V_{CE} = -5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)	N_F	–	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BCW70LT1G

TYPICAL NOISE CHARACTERISTICS

($V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

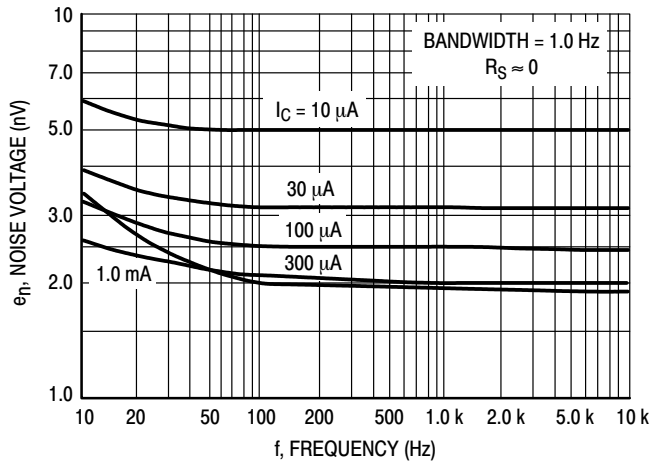


Figure 1. Noise Voltage

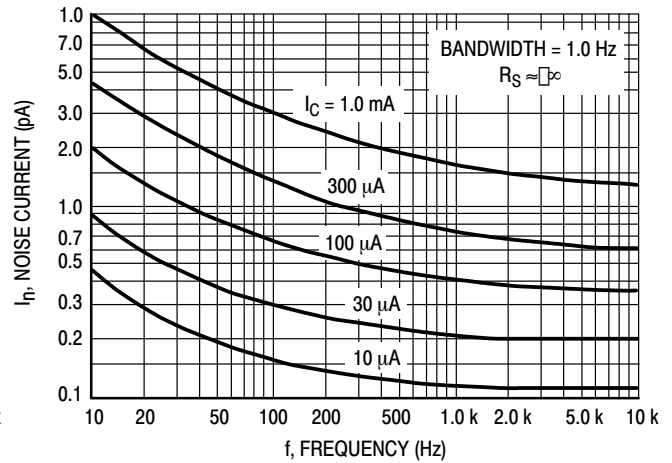


Figure 2. Noise Current

NOISE FIGURE CONTOURS

($V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

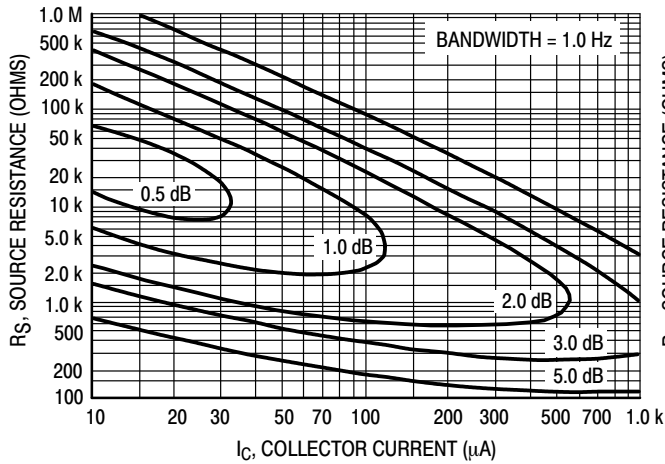


Figure 3. Narrow Band, 100 Hz

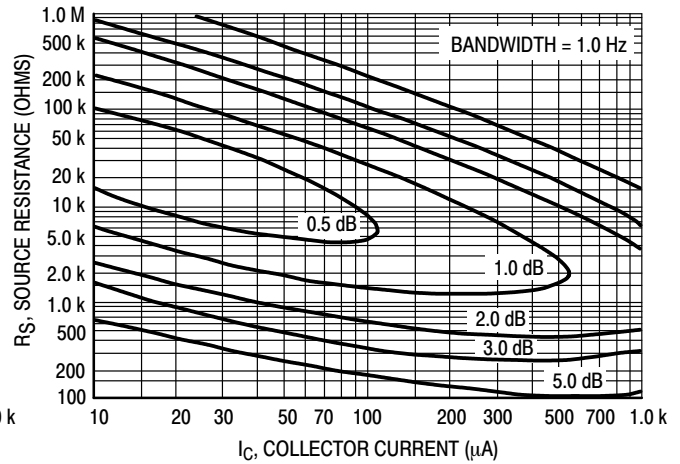


Figure 4. Narrow Band, 1.0 kHz

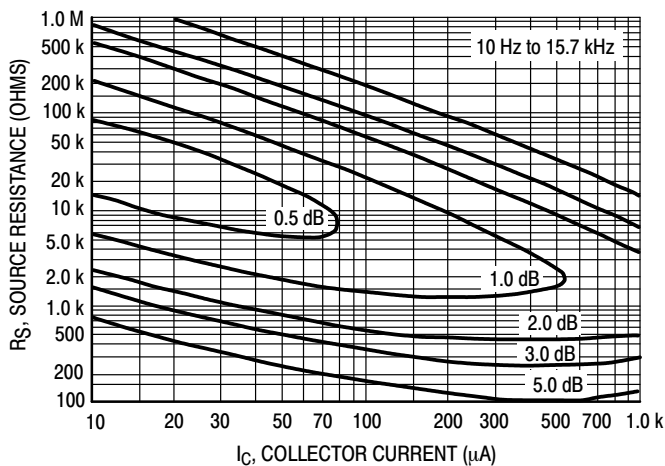


Figure 5. Wideband

Noise Figure is Defined as:

$$NF = 20 \log_{10} \left[\frac{e_n^2 + 4KTR_S + I_n^2 R_S^2}{4KTR_S} \right]^{1/2}$$

e_n = Noise Voltage of the Transistor referred to the input. (Figure 3)

I_n = Noise Current of the Transistor referred to the input. (Figure 4)

K = Boltzman's Constant ($1.38 \times 10^{-23} \text{ J/}^\circ\text{K}$)

T = Temperature of the Source Resistance ($^\circ\text{K}$)

R = Source Resistance (Ohms)

S

BCW70LT1G

TYPICAL STATIC CHARACTERISTICS

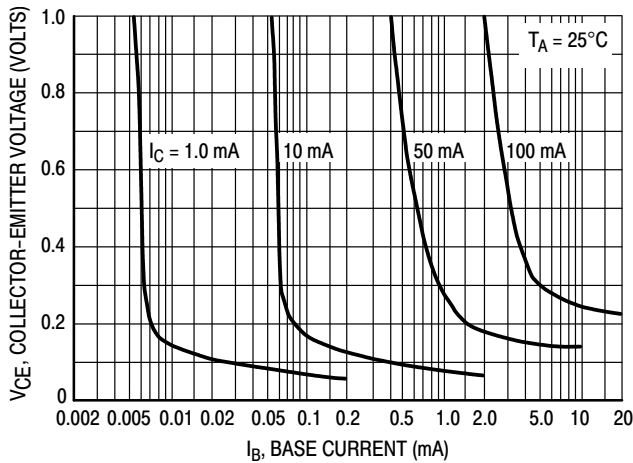


Figure 6. Collector Saturation Region

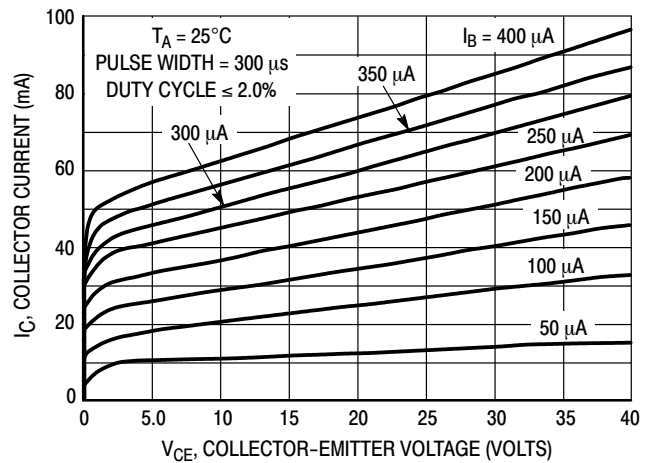


Figure 7. Collector Characteristics

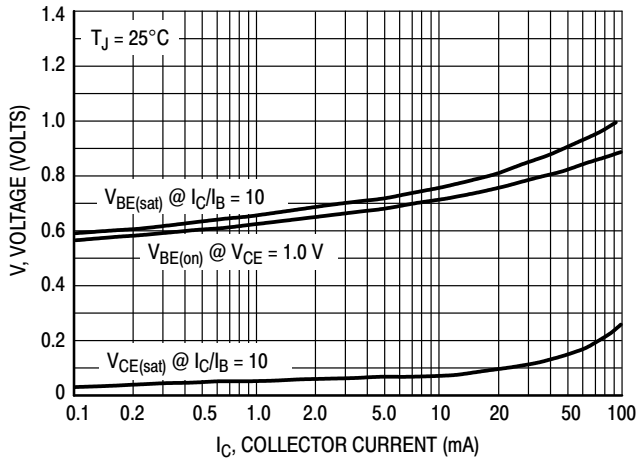


Figure 8. "On" Voltages

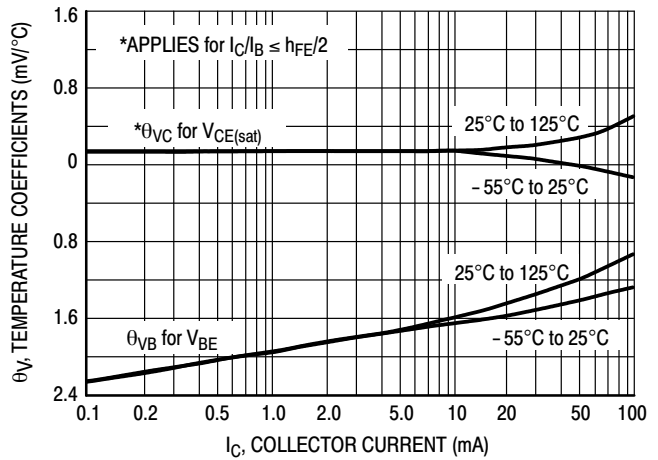


Figure 9. Temperature Coefficients

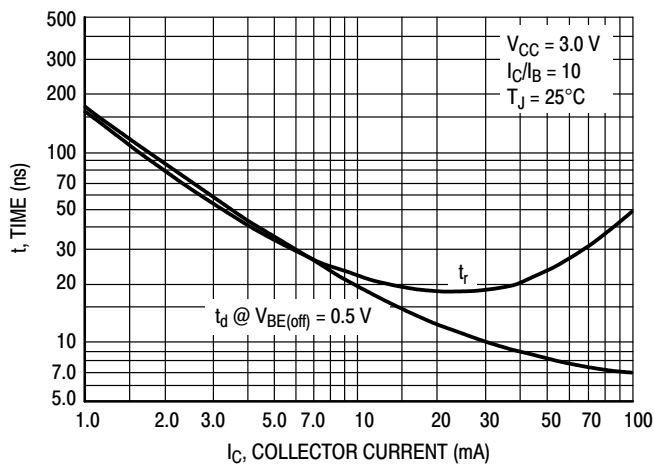


Figure 10. Turn-On Time

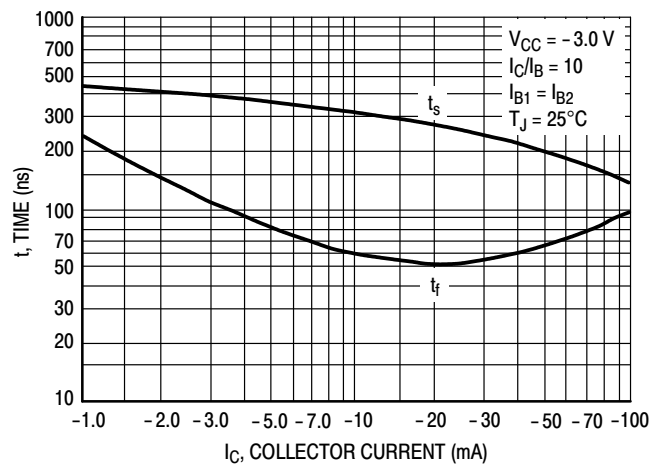


Figure 11. Turn-Off Time

BCW70LT1G

TYPICAL DYNAMIC CHARACTERISTICS

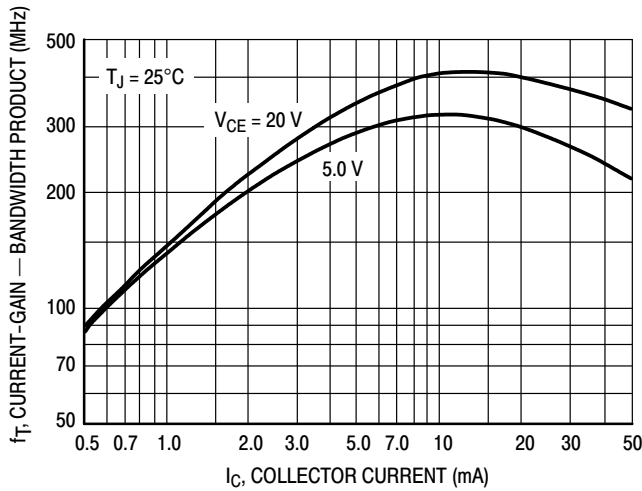


Figure 12. Current-Gain — Bandwidth Product

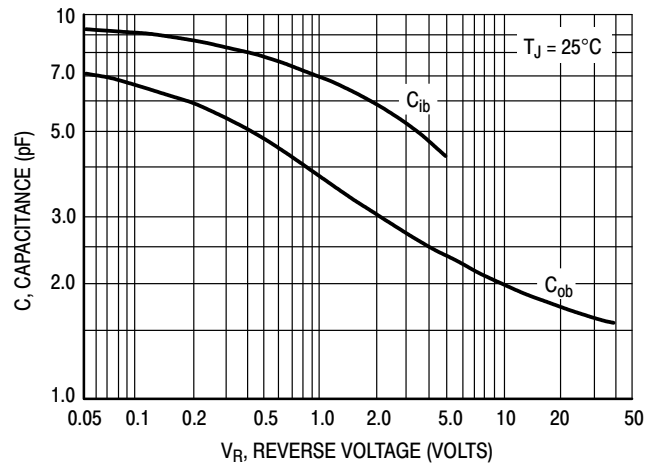


Figure 13. Capacitance

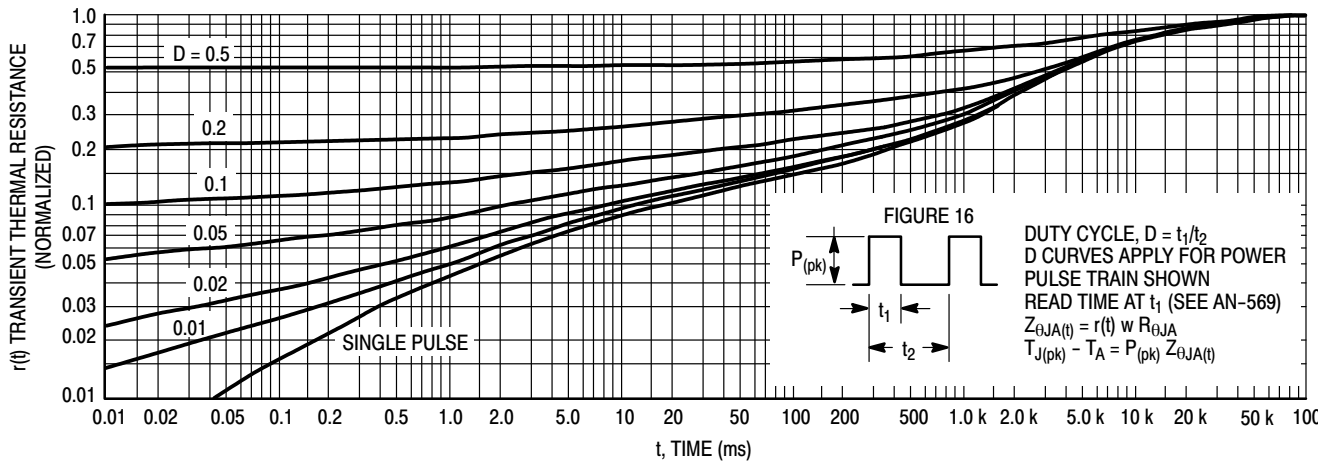


Figure 14. Thermal Response

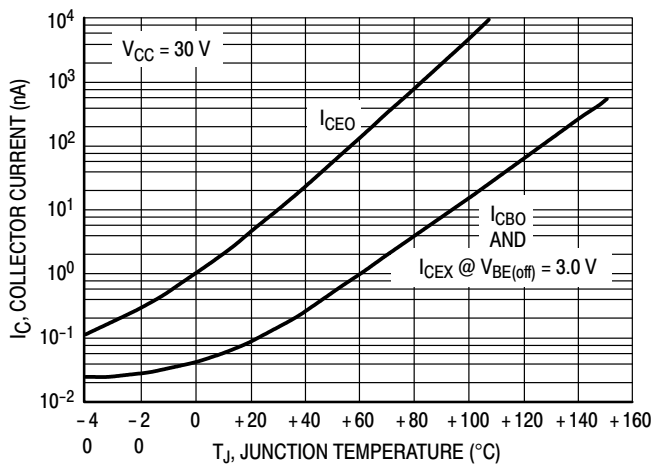


Figure 15. Typical Collector Leakage Current

DESIGN NOTE: USE OF THERMAL RESPONSE DATA

A train of periodical power pulses can be represented by the model as shown in Figure 16. Using the model and the device thermal response the normalized effective transient thermal resistance of Figure 14 was calculated for various duty cycles.

To find $Z_{\theta JA}(t)$, multiply the value obtained from Figure 14 by the steady state value $R_{\theta JA}$.

Example:

Dissipating 2.0 watts peak under the following conditions:

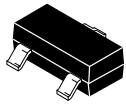
$t_1 = 1.0$ ms, $t_2 = 5.0$ ms ($D = 0.2$)

Using Figure 14 at a pulse width of 1.0 ms and $D = 0.2$, the reading of $r(t)$ is 0.22.

The peak rise in junction temperature is therefore

$$\Delta T = r(t) \times P_{(pk)} \times R_{\theta JA} = 0.22 \times 2.0 \times 200 = 88^\circ\text{C}.$$

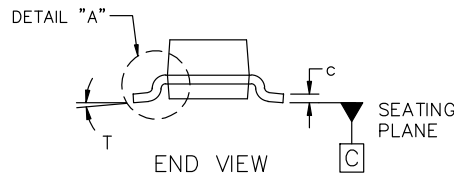
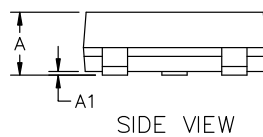
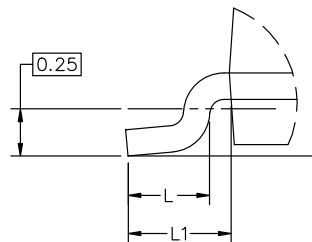
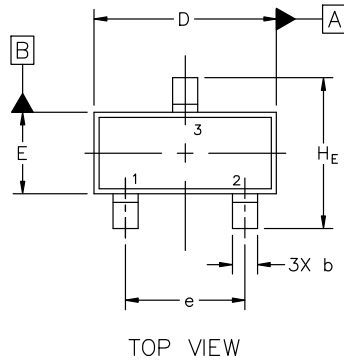
For more information, see AN-569.



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

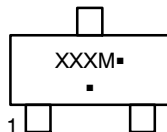
DATE 14 AUG 2024



MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

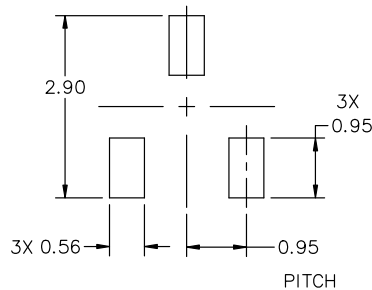
NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*


XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.


RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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DESCRIPTION:	SOT-23 (TO-236) 2.90x1.30x1.00 1.90P	PAGE 1 OF 2

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CASE 318
ISSUE AU

DATE 14 AUG 2024

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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